Description

The MIE-514H4 is a GaAlAs infrared LED having a peak wavelength at 850 nm. It feature ultra-high power, high response speed and molded in water clear plastic package, the MIE-514H4 have greatly improved long-distance characteristics as well as as significantly increased its range of applicability.

Features

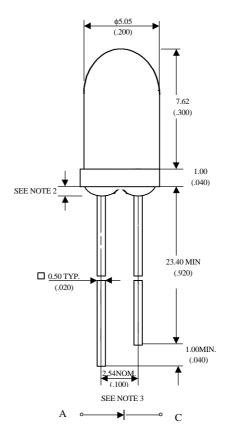
- Ultra-High radiant incidence
- High response speed
- · High modulation bandwidth
- Standard T-1 3/4 (φ5mm) package
- Radiation angle: 15°
- Peak wavelength $\lambda_p = 850 \text{ nm}$

Applications

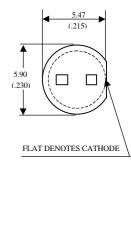
- Free air transmission systems with high -speed response
- SIR

Absolute Maximum Ratings

Package Dimensions



Unit: mm (inches)



NOTES:

- 1. Tolerance is $\pm\,0.25$ mm (.010") unless otherwise noted.
- 2. Protruded resin under flange is 1.5 mm (.059") max.
- 3. Lead spacing is measured where the leads emerge from the package.

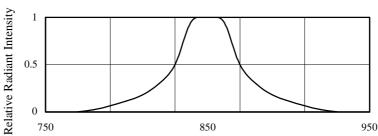
		$@ T_A = 25^\circ$	
Parameter	Maximum Rating	Unit	
Power Dissipation	120	mW	
Peak Forward Current(300pps,10µs pulse)	1	A	
Continuos Forward Current	100	mA	
Reverse Voltage	5	V	
Operating Temperature Range	-55°C to +100°C		
Storage Temperature Range	-55°C to +100°C		
Lead Soldering Temperature	260°C for 5 seconds		

Optical-Electrical Characteristics

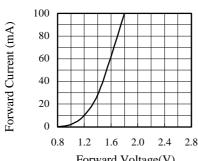
@ $T_A = 25^{\circ}C$

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Radiant Intensity	I _F =20mA	Ie		8		mW/sr
Forward Voltage	I _F =50mA	V_{F}		1.5	1.8	V
Reverse Current	$V_R=5V$	I_R			100	μΑ
Peak Wavelength	I _F =20mA	λр		850		nm
Spectral Bandwidth	I _F =20mA	Δλ		30		nm
Half View Angle	I _F =20mA	$2\theta_{1/2}$		15		deg .
Rise Time	I _F =50mA	Tr		20		nsec
Fall Time	I _F =50mA	Tf		30		nsec

Typical Optical-Electrical Characteristic Curves



Wavelength (nm)
FIG.1 SPECTRAL DISTRIBUTION



Forward Voltage(V)
FIG.2 FORWARD CURRENT VS.
FORWARD VOLTAGE

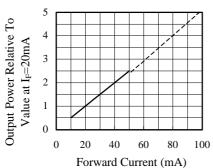


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

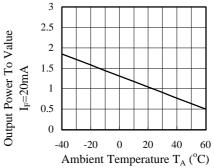


FIG.3 RELATIVE RADIANT INTENSITY
VS. AMBIENT TEMPERATURE

